
ACTIVE CIRCUIT ANALYSIS AND DESIGN

EET 214 Active Circuit Analysis and Design**4.0 UNITS**

Continuation of EET 212, Active Electronics Devices. Bipolar junction transistor (BJT) small signal multistage amplifiers, decibels, and power amplifiers are studied. Junction field effect and metal-oxide-silicon field effect transistor biasing, and small-signal operations are covered. Consideration will be given to the frequency response characteristics of BJT and JFET circuits. The experiments study the performance of small-signal amplifiers, connected in the common-emitter mode, the emitter-follower mode, and the common-based mode, followed by an analysis of cascaded RC coupled amplifiers. The analysis and design of biasing, and FET small-signal amplifiers. The final experiment is a detailed analysis of the frequency response of a transistor amplifier.